24. The semiconductor laser diode chip, as claimed in claim 21, wherein said first pair of marks comprises lines formed on an upper portion of said active layer.

25. The semiconductor laser diode chip, as claimed in claim 24, wherein said lines have a same width as that of said active layer.

26. The semiconductor laser diode chip, as claimed in claim 21, wherein said second pair of marks have a circular shape.

27. The semiconductor laser diode chip, as claimed in claim 21, wherein said pair of substrate side marks have a diameter different than a diameter of said second pair of marks.

28. The semiconductor laser diode chip, as claimed in claim 21, wherein a distance between each individual mark of said first pair of marks is 10 μm.

29. An optical module, comprising:

a substrate; and

the semiconductor laser diode chip of claim 1 formed on the substrate.

30. The module of claim 29, further comprising:

an optical fiber arranged on the substrate and connected to the semiconductor laser diode chip.

31. A semiconductor laser diode chip to be mounted on a substrate for an optical module, comprising:

an active layer;

a positioning-type mark in a vicinity of said active layer; and

a measurement-type mark located between said active layer and said positioning-type mark.

32. The semiconductor laser diode chip as claimed in claim 31, wherein said chip is positioned on said substrate by aligning said position-type mark with a another position-type mark on said substrate.

33. The semiconductor laser diode chip as claimed in claim 32, wherein said chip is positioned on said substrate by measuring a distance between said active layer and said measurement-type mark. –